

Substitute for form 1449A/PTO  
**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
(Use as many sheets as necessary)



Complete if Known

<b>Application Number</b>	09/945507
<b>Filing Date</b>	August 30, 2001
<b>First Named Inventor</b>	Forbes, Leonard
<b>Group Art Unit</b>	2824
<b>Examiner Name</b>	Dinh, Son

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Attorney Docket No: 1303.014US1

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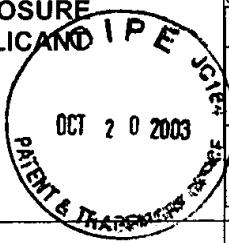
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		<b>Examiner Name</b>	Dinh, Son
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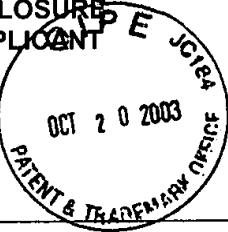
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		<b>Group Art Unit</b>	2824
		<b>Examiner Name</b>	Dinh, SOON
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